

Analysis of deep level centers in GaAs pin-diode structures

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Investigation of deep level centers in i- and n-layers of GaAs pin-diodes

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Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p⁺-pin-n⁺ structures and result of analysis

Toompuu, Jana; Sleptšuk, Natalja; Korolkov, Oleg; Rang, Toomas BEC 2016 : 2016 15th Biennial Baltic Electronics Conference : proceedings of the 15th Biennial Baltic Electronics Conference : Tallinn University of Technology, October 3-5, 2016, Tallinn, Estonia 2016 / p. 35-38 : ill http://www.eester.ee/record=b2150914*est

Spectral properties of incoherent terahertz torch based on parabolic Ga(As,Bi)/AlGaAs quantum wells

Karaliunas, Mindaugas; Pagalys, Justas; Jakštas, Vytautas; Norkus, Ričardas; Urbanowicz, Andrzej; Devenson, Jan; Devenson, Renata; **Udal, Andres**; Valušis, Gintaras Terahertz Emitters, Receivers, and Applications X : SPIE Optical Engineering + Applications, 11-15 August 2019, San Diego, California, United States : proceedings SPIE digital library 2019 <https://doi.org/10.1117/12.2528428> [Conference proceeding at Scopus](#) [Article at Scopus](#) [Article at WOS](#)